

Andrey V Zotov

List of Publications by Year in descending order

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164
papers

2,671
citations

236833

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170
docs citations

170
times ranked

2046
citing authors

#	ARTICLE	IF	CITATIONS
1	Insights Into the Electronic Properties of PbBi Atomic Layers on Ge(111) and Si(111) Surfaces. <i>Frontiers in Materials</i> , 2022, 9, .	1.2	5
2	Single and double In atomic layers grown on top of a single atomic NiSi_2 layer on Si(111). <i>Physical Review B</i> , 2022, 106, .	1.2	4
3	Structural and electronic properties of C60 fullerene network self-assembled on metal-covered semiconductor surfaces. <i>Journal of Chemical Physics</i> , 2021, 154, 104703.	1.1	9
4	One-dimensional spin-polarized electron channel in the two-dimensional PbBi compound on silicon. <i>Physical Review B</i> , 2021, 104, .	2.1	1
5	Solving a Long-Standing Problem Regarding Atomic Structure of $\text{Si}(100)2\sqrt{3}\text{-Ag}$. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 9584-9587.	7.3	6
6	Metal Sheet of Atomic Thickness Embedded in Silicon. <i>ACS Nano</i> , 2021, 15, 19357-19363.	0.7	4
7	Trivial band topology of ultra-thin rhombohedral Sb_2Se_3 grown on Bi_2Se_3 . <i>Journal of Physics Condensed Matter</i> , 2020, 32, 165001.	2.0	11
8	Fabrication and characterization of a single monolayer NiSi_2 sandwiched between a TI capping layer and a $\text{Si}(1\sqrt{3}\times 1\sqrt{3})$ substrate. <i>2D Materials</i> , 2020, 7, 025009.	0.7	2
9	Atomic, electronic and transport properties of $\text{In}\delta\text{-Au}$ 2D compound on $\text{Si}(1\sqrt{3}\times 1\sqrt{3})$. <i>Journal of Physics Condensed Matter</i> , 2020, 32, 135003.	1.1	3
10	Kondo effect at ultimate atomic-scale two-dimensional limit: $\text{Au/Si}(111) 3\sqrt{3}\text{-3}$ reconstruction with embedded Cr atoms. <i>Physical Review B</i> , 2020, 102, .	1.1	11
11	One-dimensional Rashba states in Pb atomic chains on a semiconductor surface. <i>Physical Review B</i> , 2020, 102, .	1.8	3
12	Superconducting proximity effect in a Rashba-type surface state of $\text{Pb/Ge}(111)$. <i>Superconductor Science and Technology</i> , 2020, 33, 075007.	1.1	5
13	Double-atomic-layer TI-Mg compound on a $\text{Si}(111)$ surface with advanced electronic properties. <i>Physical Review B</i> , 2020, 101, .	1.1	9
14	Au-induced reconstructions of the $\text{Si}(111)$ surface with ordered and disordered domain walls. <i>Physical Review B</i> , 2020, 101, .	2.0	17
15	Thallene: graphene-like honeycomb lattice of TI atoms frozen on single-layer NiSi_2 . <i>2D Materials</i> , 2020, 7, 045026.	1.1	6
16	Superconductor-insulator transition in an anisotropic two-dimensional electron gas assisted by one-dimensional Friedel oscillations: TI-Mg . <i>Physical Review B</i> , 2019, 100, .	0.7	1
17	Observation of the nesting and defect-driven 1D incommensurate charge density waves phase in the 2D system. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 115402.	4.5	9
18	Weak Antilocalization at the Atomic-Scale Limit of Metal Film Thickness. <i>Nano Letters</i> , 2019, 19, 570-575.		

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19	Surface Science. , 2019, , 23-45.		0
20	Double-atomic layer of Tl on Si(111): Atomic arrangement and electronic properties. Surface Science, 2018, 668, 17-22.	0.8	9
21	(Tl, Au)/Si(111) $\sqrt{7} \times \sqrt{7}$ 2D compound: an ordered array of identical Au clusters embedded in Tl matrix. Journal of Physics Condensed Matter, 2018, 30, 025002.	0.7	4
22	Thickness Dependence of Surface Structure and Superconductivity in Pb Atomic Layers. Journal of the Physical Society of Japan, 2018, 87, 113601.	0.7	2
23	Two-dimensional metallic (Tl,Au)/Si(100)c(2 \times 2) : A Rashba-type system with C2v symmetry. Physical Review B, 2018, 98, .	1.1	5
24	Unconventional superconductivity in the single-atom-layer alloy Si(111) $\sqrt{3} \times \sqrt{3}$ (Tl,Pb). Physical Review B, 2018, 98, .	1.1	13
25	Electronic properties of the two-dimensional (Tl, Rb)/Si(111) $\sqrt{3} \times \sqrt{3}$ compound having a honeycomb-like structure. Journal of Physics Condensed Matter, 2018, 30, 415502.	0.7	3
26	Studying the Surface Conductivity of a Thallium Bilayer on Si(111) Substrate after Adsorption of Lithium and Rubidium. Technical Physics Letters, 2018, 44, 412-415.	0.2	1
27	From C60 to C ₆₀ Fullerene Self-assembly of 2D fullerene nanostructures on metal-covered silicon and germanium. Journal of Chemical Physics, 2018, 149, 034702.	1.2	7
28	Two-Dimensional In ₂ Sb Compound on Silicon as a Quantum Spin Hall Insulator. Nano Letters, 2018, 18, 4338-4345.	4.5	23
29	Superconductivity in thallium double atomic layer and transition into an insulating phase intermediated by a quantum metal state. 2D Materials, 2017, 4, 025020.	2.0	30
30	2D Tl ₂ Pb compounds on Ge(111) surface: atomic arrangement and electronic band structure. Journal of Physics Condensed Matter, 2017, 29, 035001.	0.7	3
31	One-atom-layer compounds on silicon and germanium. Japanese Journal of Applied Physics, 2017, 56, 08LA01.	0.8	14
32	Theory versus experiment for a family of single-layer compounds with a similar atomic arrangement: <mml:math		

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37	Comparative STM analysis of C60 and C70 fullerene adsorption sites on pristine and Al-modified Si(111) $\sqrt{7} \times \sqrt{7}$ surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 061402.	0.8	3
38	Bismuth-indium two-dimensional compounds on Si(111) surface. Surface Science, 2016, 651, 105-111.	0.8	19
39	Magnetoresistive properties of nanostructured magnetic metals, manganites, and magnetic semiconductors. Technical Physics, 2016, 61, 233-239.	0.2	2
40	Low-temperature one-atom-layer $\sqrt{7} \times \sqrt{7}$ -In phase on Si(111). Surface Science, 2016, 649, 14-19.	0.8	12
41	Observation of Superconductivity on the Rashba-Type Surface Reconstruction (Tl, Pb)/Si(111) by <i>in situ</i> Electrical Transport Measurements. Hyomen Kagaku, 2016, 37, 363-368.	0.0	0
42	Scanning tunneling microscopy observation of ultrathin epitaxial CoSi ₂ (111) films grown at a high temperature. Technical Physics, 2015, 60, 1508-1514.	0.2	9
43	Atomic structure and electronic properties of the two-dimensional $\sqrt{2} \times \sqrt{2}$ Au/Si(111) surface. Physical Review B, 2015, 92, .	0.2	1
44	Two-Dimensional Superconductor with a Giant Rashba Effect: One-Atom-Layer Tl-Pb Compound on Si(111). Physical Review Letters, 2015, 115, 147003.	2.9	108
45	Direct observation of a gap opening in topological interface states of MnSe/Bi ₂ Se ₃ heterostructure. Applied Physics Letters, 2015, 107, .	1.5	28
46	Incommensurate superstructure in heavily doped fullerene layer on Bi/Si(111) surface. Journal of Chemical Physics, 2015, 143, 074707.	1.2	1
47	Electronic band structure of a Tl/Sn atomic sandwich on Si(111). Physical Review B, 2015, 91, .	1.1	25
48	Magic C60 islands forming due to moiré interference between islands and substrate. Surface Science, 2015, 635, 94-98.	0.8	5
49	Electrical conductivity of reconstructed Si(111) surface with sodium-doped C60 layers. Applied Physics Letters, 2015, 106, 011603.	1.5	1
50	Self-assembled C60 layers on incommensurate Cu/Si(111) $\sqrt{5} \times \sqrt{5}$ pseudo- $\sqrt{5} \times \sqrt{5}$ surface. Surface Science, 2015, 642, 6-10.	0.8	2
51	Atomic arrangement and electron band structure of Si(1 1 1)- $\sqrt{3} \times \sqrt{3}$ -Bi reconstruction modified by alkali-metal adsorption: an initial study. Journal of Physics Condensed Matter, 2015, 27, 305003.	0.7	6
52	Tailoring of spin-split metallic surface-state bands on silicon. Journal of Electron Spectroscopy and Related Phenomena, 2015, 201, 81-87.	0.8	8
53	Atomic structure and electronic properties of the In/Si(111) $\sqrt{2} \times \sqrt{2}$ surface. Structure of the Co/Si(111) $\sqrt{10} \times \sqrt{10}$ surface.	1.1	18
54	Structure of the Co/Si(111) $\sqrt{10} \times \sqrt{10}$ surface.	0.8	4

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55	Size distributions of fullerene surface clusters. Applied Surface Science, 2014, 307, 46-51.	3.1	13
56	Effect of Na adsorption on the structural and electronic properties of Si(111) $\sqrt{3}\times\sqrt{3}$ -Au surface. Journal of Physics Condensed Matter, 2014, 26, 055009.	0.7	9
57	<small>xmlns:xocs="http://www.elsevier.com/xml/xocs/dtd" xmlns:xs="http://www.w3.org/2001/XMLSchema" xmlns:xsi="http://www.w3.org/2001/XMLSchema-instance" xmlns="http://www.elsevier.com/xml/ja/dtd" xmlns:ja="http://www.elsevier.com/xml/ja/dtd" xmlns:mml="http://www.w3.org/1998/Math/MathML" xmlns:tb="http://www.elsevier.com/xml/common/table/dtd" xmlns:tbl_struct="http://www.elsevier.com/xml/common/struct-bib/dtd" xmlns:ce="http://www.elsevier.co.</small> Ap	3.1	10
58	Two-dimensional bismuth $\sqrt{3}\times\sqrt{3}$ silver structures on Si(111). Surface Science, 2014, 623, 17-24.	0.8	15
59	A Strategy to Create Spin-Split Metallic Bands on Silicon Using a Dense Alloy Layer. Scientific Reports, 2014, 4, 4742.	1.6	65
60	Stepwise self-assembly of C ₆₀ mediated by atomic scale moiré magnifiers. Nature Communications, 2013, 4, 1679.	5.8	31
61	<small>Dim C60 fullerenes on Si(111) <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si7.gif" overflow="scroll"><mml:mrow><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mo>Å</mml:mo><mml:msqrt><mml:mn>3</mml:mn></mml:msqrt><mml:mi>Ag</mml:mi></mml:mrow></mml:math></small> surface. Surface Science, 2013, 612, 31-36.	0.8	12
62	Peculiar diffusion of C ₆₀ on In-adsorbed Si(111) $\sqrt{3}\times\sqrt{3}$ -Au surface. Surface Science, 2013, 616, 44-50.	0.8	12
63	Large spin splitting of metallic surface-state bands at adsorbate-modified gold/silicon surfaces. Scientific Reports, 2013, 3, 1826.	1.6	51
64	Structural transformations in Pb/Si(111) phases induced by C ₆₀ adsorption. Journal of Physics Condensed Matter, 2013, 25, 395006.	0.7	7
65	Modification of the sample holder for a variable temperature scanning tunneling microscope (Omicron). Instruments and Experimental Techniques, 2013, 56, 745-748.	0.1	0
66	The manipulation of C ₆₀ in molecular arrays with an STM tip in regimes below the decomposition threshold. Nanotechnology, 2013, 24, 055302.	1.3	11
67	ELECTRICAL CONDUCTIVITY STUDY OF Au AND Na COADSORBED Si(111) $\sqrt{3}\times\sqrt{3}$ SURFACE. , 2013, , .		0
68	Ordered Mn-diluted Au/Si(111) reconstructions. Surface Science, 2012, 606, 104-109.	0.8	3
69	Self-assembly of C ₆₀ fullerenes on quasi-one-dimensional Si(111) $\sqrt{4}\times\sqrt{1}$ -In surface. Surface Science, 2012, 606, 1821-1824.	0.8	10
70	First-principles study of Si(111)-In reconstruction. Surface Science, 2012, 606, 1914-1917.	0.8	7
71	Characterization of Si(111)-(Au,In) surface by optical second-harmonic generation. Applied Surface Science, 2012, 258, 4642-4644.	3.1	1
72	Surface conduction at phase transitions in (Au,Ag)/Si(111) submonolayer films. Applied Surface Science, 2012, 258, 9636-9641.	3.1	3

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73	Formation and properties of thin films of iron silicides on Si(111) Surface: Ab initio simulation. Technical Physics Letters, 2012, 38, 215-217. Modulated C_{60} on Si(111) surface. Journal of Applied Physics, 2011, 110, 083505.	0.2	1
74	on Si(111) C_{60} on Si(111) surface. Surface Science, 2011, 605, 1951-1955.	1.1	23
75	Optimal Cu buffer layer thickness for growing epitaxial Co overlayers on Si(111) C_{60} on Si(111) surface. Surface Science, 2011, 605, 1951-1955.	1.1	10
76	C60 adsorption onto the one-atomic-layer In films on Si(111) surface. Surface Science, 2011, 605, 1951-1955.	0.8	12
77	Interplay between adsorbed C60 fullerenes and point defects on a Si(111) C_{60} on Si(111) surface. Surface Science, 2011, 605, 2050-2054.	0.8	6
78	Effect of C60 layer on the growth mode and conductance of Au and Ag films on Si(111)3-Au and Si(111)3-Ag surfaces. Journal of Applied Physics, 2011, 110, 093704.	1.1	10
79	Variable termination of MnSi/Si(111) C_{60} on Si(111) surface. Surface Science, 2011, 605, 289-295.	0.8	13
80	Structural transformations in (Au,In)/Si(111) system and their effect on surface conductivity. Surface Science, 2011, 605, 1420-1425.	0.8	11
81	Broken Even-Odd Symmetry in Self-Selection of Distances between Nanoclusters due to the Presence or Absence of Topological Solitons. Physical Review Letters, 2011, 106, 166101.	2.9	3
82	Effect of Si(100)-c(4 $\sqrt{3}$ \times 12)-Al and Si(111)-(5.55 $\sqrt{3}$ \times 5.55)-Cu reconstructions on the deposition of cobalt onto silicon surface. Technical Physics Letters, 2010, 36, 100-103.	0.2	3
83	Peculiarities of Al magic cluster self-assembly on Si(1 0 0) surface. Surface Science, 2010, 604, 674-678.	0.8	0
84	Diffusion and clustering of adatoms on discommensurate surface template: Ge atoms on Si(1 1 1) $\sqrt{3}$ \times $\sqrt{3}$ \times 5 $\sqrt{3}$ -Cu reconstruction. Surface Science, 2010, 604, 666-673.	0.8	5
85	Cooperative phenomena in self-assembled nucleation of 3 $\sqrt{3}$ \times 4-In/Si(100) surface magic clusters. Surface Science, 2010, 604, 1116-1120.	0.8	2
86	Atomic and electronic structures of Ag/Si(100)-c(6 $\sqrt{3}$ \times 2) surface: A first-principles study. Surface Science, 2010, 604, 1400-1405.	0.8	5
87	Effect of Surface Potential Relief on Forming Molecular Arrays: Tryptanthrin Adsorbed on Various Si(111) Reconstructions. Journal of Physical Chemistry C, 2010, 114, 14489-14495.	1.5	10
88	Growth of Au thin film on Cu-modified Si(111) surface. Surface Science, 2009, 603, 3400-3403.	0.8	5
89	Structural properties of Cu clusters on Si(111):Cu ₂ Si magic family. Surface Science, 2009, 603, 2874-2878.	0.8	14
90	Ab initio computer simulation of adsorption of a Fe monolayer on Si(111). Technical Physics, 2009, 54, 1561-1565.	0.2	3

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91	Multi-mode growth in Cu/Si(111) system: Magic nanoclustering, layer-by-layer epitaxy and nanowire formation. Surface Science, 2008, 602, 391-398.	0.8	30
92	Self-assembly of conductive Cu nanowires on Si(111)-5 TM -Cu surface. Nanotechnology, 2008, 19, 245608.	1.3	7
93	Relative stabilities of adsorbed versus substitutional Al atoms in submonolayer Al on Si(111). Physical Review B, 2008, 78, .	1.1	1
94	Random and ordered arrays of surface magic clusters. International Reviews in Physical Chemistry, 2008, 27, 317-360.	0.9	24
95	Developing antiphase boundaries in one-monolayer Al on Si(111). Physical Review B, 2007, 76, .	1.1	1
96	Pb-modified $\text{In-Si}(100)4\text{\AA}$ -3 magic clusters: Scanning tunneling microscopy and first-principles total-energy calculations. Physical Review B, 2007, 76, .	1.1	3
97	Tl/Ge(100) system: Phase formation and phase transitions. Surface Science, 2007, 601, 595-602.	0.8	2
98	Growth of copper nanoislands on the Si(100)-c(4 \times 12)-Al surface studied by scanning tunneling microscopy. Technical Physics Letters, 2007, 33, 912-914.	0.2	2
99	A cooling system for samples for studying their surfaces in ultrahigh vacuum. Instruments and Experimental Techniques, 2006, 49, 141-143.	0.1	2
100	Growth of In nanocrystallite arrays on the Si(100)-c(4 \times 12)-Al surface. Surface Science, 2006, 600, 4986-4991.	0.8	4
101	Diverse magic nanoclustering in submonolayer Tl/Si(111) system. Surface Science, 2006, 600, 1936-1941.	0.8	17
102	Comparative STM study of SPE growth of FeSi ₂ nanodots on Si(111)7 \times 7 and -R30 \times -B surfaces. Surface Science, 2006, 600, 2623-2628.	0.8	4
103	Atomic dynamics of In nanoclusters on Si(100). Physical Review B, 2006, 74, .	1.1	4
104	Reversible phase transitions in the pseudomorphic 7 \times 3-hex In layer on Si(111). Physical Review B, 2006, 74, .	1.1	31
105	Si(111)-3 \times 3 \times 3 \times phase modified by In adsorption: Stabilization of a homogeneous surface by stress relief. Physical Review B, 2006, 73, .	1.1	44
106	Formation of Si nanodot arrays on the oxidized Si(100) surface. Applied Surface Science, 2005, 243, 199-203.	3.1	8
107	Self-assembly formation of the ordered nanostructure arrays induced by Be interaction with Si(111) surface. Surface Science, 2005, 574, 99-109.	0.8	5

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109	Modified Si(100)4Å—3-In nanocluster arrays. Surface Science, 2005, 598, 136-143.	0.8	5
110	STM study of the early stages of the Cr/Si(111) interface formation. Surface Science, 2005, 596, 53-60.	0.8	15
111	In situREM and ex situSPM studies of silicon (111) surface. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 2344-2354.	0.8	3
112	Growth of thallium overlayers on a Si(100) surface. Physical Review B, 2005, 71, .	1.1	23
113	Long-period modulations in the linear chains of Tl atoms on Si(100). Physical Review B, 2005, 71, .	1.1	13
114	Submonolayer Er Phases on Si(111). Japanese Journal of Applied Physics, 2004, 43, 1110-1113.	0.8	7
115	Quantitative characterization of the Al nanoclustering induced by H interaction with Si(100)c(4Å—12)-Al surface phase. Surface Science, 2004, 565, 121-128.	0.8	6
116	Tl overlayers on Si(100) and their self-assembly induced by STM tip. Applied Surface Science, 2004, 237, 110-114.	3.1	8
117	Ordered Arrays of Be-Encapsulated Si Nanotubes on Si(111) Surface. Nano Letters, 2004, 4, 1469-1473.	4.5	29
118	Thallium overlayers on Si(111) studied by scanning tunneling microscopy. Surface Science, 2003, 543, L663-L667.	0.8	32
119	Atomic structure of the Si(111)-Al phase studied using STM and total-energy calculations. Surface Science, 2003, 545, L779-L783.	0.8	6
120	Surface Science. Advanced Texts in Physics, 2003, , .	0.5	325
121	Doping of Magic Nanoclusters in the SubmonolayerIn/Si(100)System. Physical Review Letters, 2003, 91, 026104.	2.9	21
122	Effect of Substrate Surface Phase on the Shape of Self-Organized Al Nanoclusters on Si(100) Formed upon Atomic Hydrogen Exposure. Japanese Journal of Applied Physics, 2003, 42, L432-L434.	0.8	4
123	Magic nanoclusters of group III metals on Si(100) surface. E-Journal of Surface Science and Nanotechnology, 2003, 1, 33-40.	0.1	13
124	Formation of the ordered array of Al magic clusters on Si(111)7Å—7. Physical Review B, 2002, 66, .	1.1	122
125	High-temperature interaction of Al with Si(100) surface at low Al coverages. Surface Science, 2002, 506, 80-86.	0.8	9
126	Structure of domain walls in Al/Si(100) β -phase. Surface Science, 2002, 517, 151-156.	0.8	14

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127	Surface Phases of Metals on Silicon as Material for Surface Engineering. Materials Research Society Symposia Proceedings, 2001, 697, 5281.	0.1	0
128	Scanning Tunneling Microscopy Study of the (4×4) Structure Formation in the Sub-Monolayer Sb/Si(100) System. Japanese Journal of Applied Physics, 2001, 40, 6069-6072.	0.8	3
129	Surface roughening at the one-monolayer Sb/Si(100) interface. Physical Review B, 2001, 65, .	1.1	9
130	Formation of a (8×2) surface phase using H-induced self-organization and H extraction. Physical Review B, 2001, 64, .	1.1	7
131	Mg/Si(100) Reconstructions Studied by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 2000, 39, 3740-3743.	0.8	11
132	Atomic-hydrogen-induced self-organization of Si(111)- $\sqrt{3} \times \sqrt{3}$ -In surface phase studied by CAICISS and STM. Surface Science, 2000, 447, 117-125.	0.8	4
133	a surface phase with a variable composition. Surface Science, 2000, 447, 15-24.	0.8	9
134	Composition and atomic structure of the surface. Surface Science, 2000, 450, 34-43.	0.8	16
135	Adsorption of atomic hydrogen on the Si(001) 4×3 -In surface studied by coaxial impact collision ion scattering spectroscopy and scanning tunneling microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 983.	1.6	7
136	Analysis of surface structures through determination of their composition using STM: Si(100)- 4×3 -In and Si(111)- 4×1 -In reconstructions. Physical Review B, 1999, 60, 14372-14381.	1.1	50
137	Hydrogen interaction with clean and modified silicon surfaces. Surface Science Reports, 1999, 35, 1-69.	3.8	209
138	Family of the metal-induced Si(111)- $\sqrt{3} \times \sqrt{3}$ -1 reconstructions with a top Si atom density of $4/3$ monolayer. Surface Science, 1999, 426, 298-307.	0.8	62
139	Ag-induced structural transformations on Si(111): quantitative investigation of the Si mass transport. Surface Science, 1999, 429, 127-132.	0.8	27
140	Mg-induced Si(111)- $(\sqrt{3} \times \sqrt{3})$ reconstruction studied by scanning tunneling microscopy. Surface Science, 1998, 415, L971-L975.	0.8	52
141	The role of Si atoms in In/Si(111) surface phase formation. Surface Science, 1998, 398, 60-69.	0.8	18
142	Atomic Hydrogen Interaction with the Si(100)- 4×3 -In Surface Studied by Scanning Tunneling Microscopy. Japanese Journal of Applied Physics, 1998, 37, 3774-3777.	0.8	7
143	Reexamination of the Si(111)- $\sqrt{3} \times \sqrt{3}$ -1 reconstruction on the basis of Si atom density and unit cluster determination. Physical Review B, 1998, 58, 3545-3548.	1.1	38
144	Structural model for the Si(100)- 4×3 -In surface phase. Physical Review B, 1998, 57, 12492-12496.	1.1	29

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145	Electrical properties of buried B/Si surface phases. Journal of Applied Physics, 1998, 83, 5865-5869.	1.1	3
146	Scanning tunneling microscopy of the $7\sqrt{3}\sqrt{3}\sqrt{3}$ - 1 transformation induced on the Si(111) surface by Na adsorption. Physical Review B, 1998, 58, 7059-7063.	1.1	18
147	Si(100) $2\sqrt{3}\sqrt{3}\sqrt{3}$ - 1 surface phase: Formation and atomic arrangement. Physical Review B, 1998, 58, 4972-4976.	1.1	25
148	Structural model for the Si(111)- $4\sqrt{3}\sqrt{3}\sqrt{3}$ - 1 In reconstruction. Physical Review B, 1997, 56, 1017-1020.	1.1	46
149	Structural transformations at room temperature adsorption of In on Si(111)- $3\sqrt{3}\sqrt{3}\sqrt{3}$ - 1 In surface: LEED-AES-STM study. Surface Science, 1997, 388, 299-307.	0.8	31
150	Si(100) $4\sqrt{3}\sqrt{3}\sqrt{3}$ - 3 In surface phase: identification of silicon substrate atom reconstruction. Surface Science, 1997, 391, L1188-L1193.	0.8	27
151	Structural defects of the Si(111)- $3\sqrt{3}\sqrt{3}\sqrt{3}$ - 1 B surface studied by scanning tunneling microscopy. Surface Science, 1996, 345, 313-319.	0.8	19
152	Epitaxial growth of ultrathin Si caps on Si(100):B surface studied by scanning tunneling microscopy. Applied Physics Letters, 1996, 69, 494-496.	1.5	12
153	Scanning tunneling microscopy study of Si growth on a Si(111)- $3\sqrt{3}\sqrt{3}\sqrt{3}$ - 3 B surface. Physical Review B, 1996, 53, 12902-12906.	1.1	26
154	B/Si(100) surface: Atomic structure and epitaxial Si overgrowth. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2684.	1.6	17
155	Electrical properties of surface phases on silicon capped by amorphous Si layers. Applied Physics Letters, 1995, 67, 611-613.	1.5	5
156	Empirical dielectric function of amorphous materials for spectroscopic ellipsometry. Journal of Applied Physics, 1995, 77, 4673-4676.	1.1	20
157	LEED-AES reexamination of the Al/Si(111) $\sqrt{3}\sqrt{3}\sqrt{3}$ -phase. Surface Science, 1994, 316, L1034-L1038.	0.8	14
158	Solid phase epitaxial growth of Si on Si $\sqrt{3}\sqrt{3}\sqrt{3}$ -Sb surface phases for the formation of $\sqrt{3}$ -doped layers and $\sqrt{3}$ -superlattices. Surface Science, 1990, 230, L147-L150.	0.8	20
159	Solid Phase Epitaxy of Doped Silicon Films in Molecular Beam Epitaxy Systems. Physica Status Solidi A, 1987, 103, 467-473.	1.7	5
160	Thermal annealing behaviour of Si/SiO ₂ structures. Thin Solid Films, 1986, 135, 99-105.	0.8	11
161	Solid phase epitaxial growth anisotropy of vacuum-deposited amorphous silicon. Physica Status Solidi A, 1984, 82, 345-353.	1.7	12
162	Epitaxial Regrowth of Amorphous Si Deposited on Si(111). Physica Status Solidi A, 1982, 72, 391-398.	1.7	14

#	ARTICLE	IF	CITATIONS
163	Characterization of In/Si(111) System by Optical Second-Harmonic Generation. Solid State Phenomena, 0, 247, 73-75.	0.3	0
164	Metals on semiconductors. , 0, , 259-283.		3